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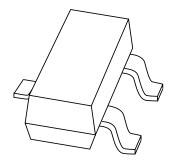
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BAL99High-speed diode

Product data sheet Supersedes data of 1999 May 26 2003 Dec 12



High-speed diode

BAL99

FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 70 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

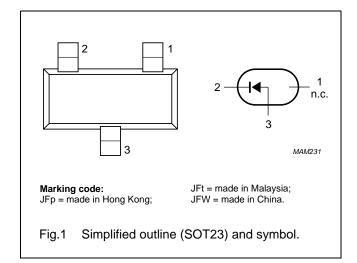
• High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

The BAL99 is a high-speed switching diode fabricated in planar technology, and encapsulated in the small SOT23 plastic SMD package.

PINNING

PIN	DESCRIPTION
1	not connected
2	cathode
3	anode



ORDERING INFORMATION

TYPE NUMBER	PACKAGE				
ITPE NUMBER	NAME	DESCRIPTION	VERSION		
BAL99	_	plastic surface mounted package; 3 leads	SOT23		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		_	70	V
V _R	continuous reverse voltage		_	70	V
I _F	continuous forward current	see Fig.2; note 1	_	215	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t _p = 1 μs	_	4	Α
		$t_p = 1 \text{ ms}$	_	1	Α
		t _p = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V _F	forward voltage	see Fig.3		
		I _F = 1 mA	715	mV
		I _F = 10 mA	855	mV
		I _F = 50 mA	1	V
		I _F = 150 mA	1.25	V
I_R	reverse current	see Fig.5		
		V _R = 25 V	30	nA
		V _R = 70 V	1	μΑ
		V _R = 25 V; T _j = 150 °C	30	μΑ
		$V_R = 70 \text{ V}; T_j = 150 ^{\circ}\text{C};$	50	μΑ
C _d	diode capacitance	$f = 1 \text{ MHz}$; $V_R = 0$; see Fig.6	1.5	pF
t _{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	4	ns
V _{fr}	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.8	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-tp)}	thermal resistance from junction to tie-point		360	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

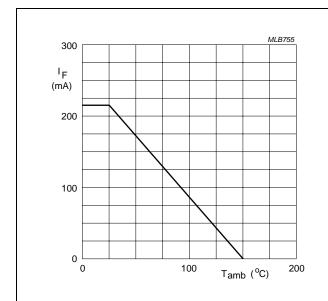
Note

1. Device mounted on an FR4 printed-circuit board.

High-speed diode

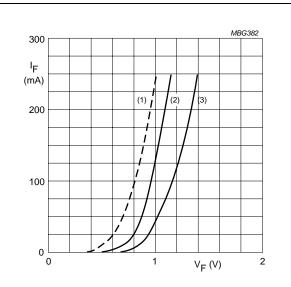
BAL99

GRAPHICAL DATA



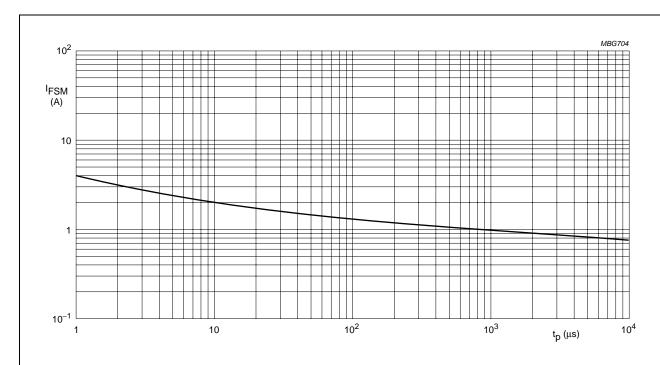
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) T_i = 150 °C; typical values.
- (2) $T_j = 25 \,^{\circ}\text{C}$; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

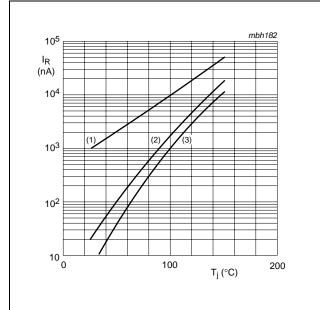


Based on square wave currents; T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

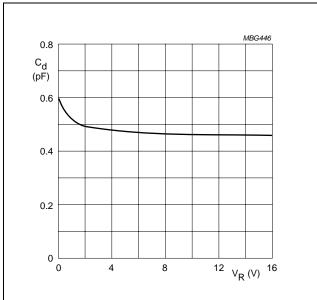
High-speed diode

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- (1) $V_R = 70 \text{ V}$; maximum values.
- (2) $V_R = 70 \text{ V}$; typical values.
- (3) $V_R = 25 \text{ V}$; typical values.

Fig.5 Reverse current as a function of junction temperature.

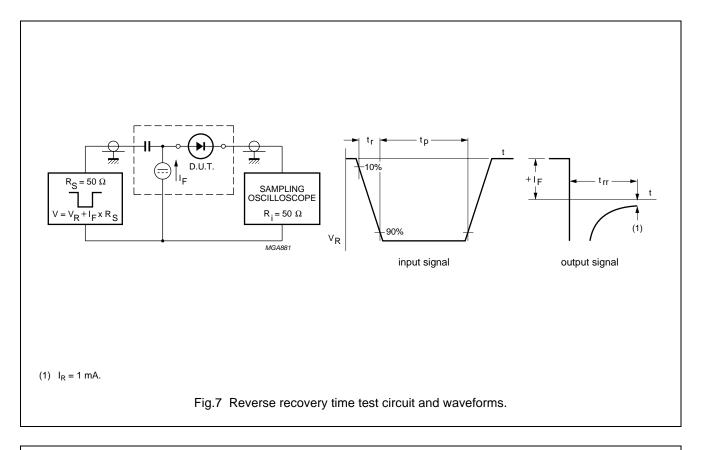


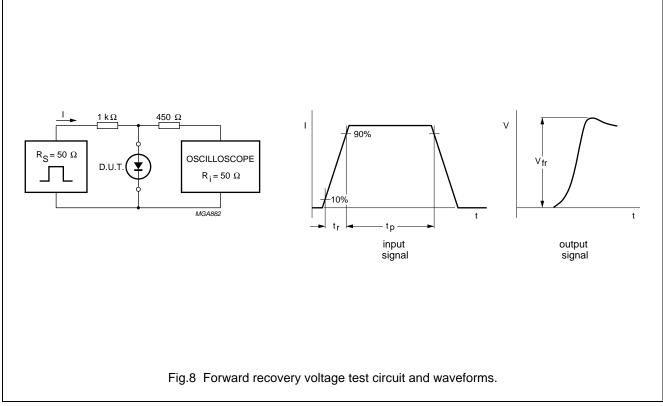
f = 1 MHz; $T_j = 25$ °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

High-speed diode

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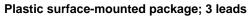




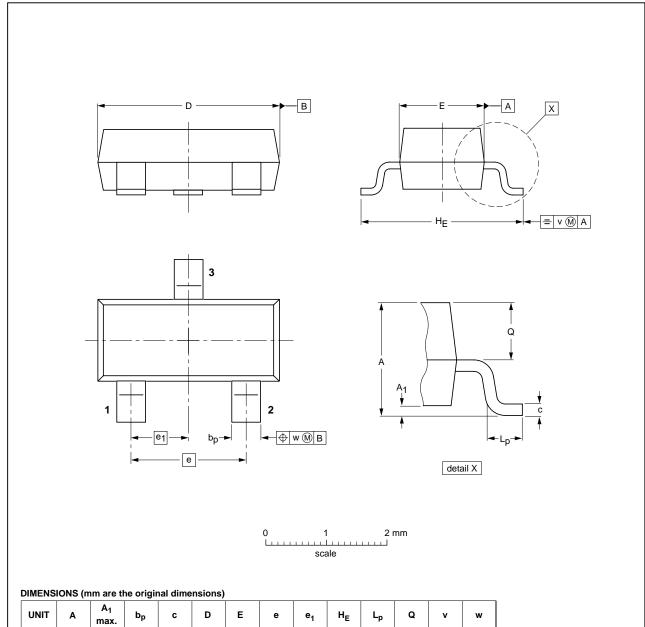
High-speed diode

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PACKAGE OUTLINE



SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUIT DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

0.45

0.1

2003 Dec 12 7

0.38

0.9

High-speed diode

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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